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a second interconnection formed over said plug;
a predetermined void between said plug and said second interconnection; and
a second dielectric film covering said second interconnection, wherein said predetermined void separates said plug from said second interconnection.

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6. (Twice Amended) A semiconductor device comprising:
a substrate;
a first interconnection formed on said substrate;
a first dielectric film covering said first interconnection;
an opening section extending from a surface of said first dielectric film to said first interconnection, said opening section being formed in said first dielectric film;
a plug formed in said opening section and electrically connected to said first interconnection;
a second interconnection formed on said first dielectric film in the vicinity of said plug ;
a second dielectric film covering said second interconnection; and
a predetermined void in said second dielectric film and located at a position adjacent to said second interconnection and at a position directly over and above said plug.

REMARKS

At the time of the Office Action dated November 11, 2002, claims 1-18 were pending in this application. Claims 1 and 6 have been amended. Care has been exercised to avoid the introduction of new matter. The amendments to claims 1 and 6 clarify the limitations recited therein. Applicant submits that the present Amendment does not generate any new matter issue.